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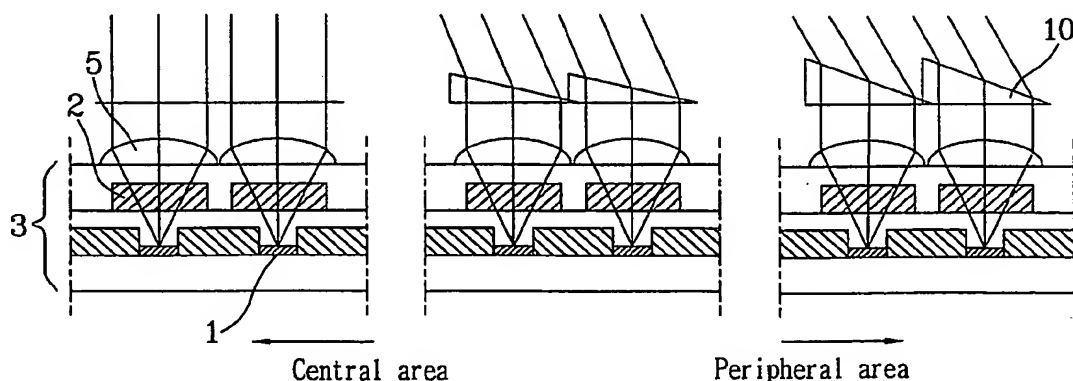
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(54) Title: **IMAGE SENSOR AND METHOD FOR FABRICATING THE SAME**



(57) Abstract: An image sensor includes a substrate in which photoelectric elements have been formed, and an array of optical path conversion elements formed at a light so that the optical path converted light may be incident on the substrate, wherein each of the optical path conversion elements has different tangent line gradients on the corresponding parts of incident surfaces according to distances from the center of the image sensor in order to compensate for differences of incident angles of incident light according to the distances from the center of the image sensor. In addition, a method for fabricating the image sensor fabricates the optical path conversion elements according to a photolithography process using a gray scale mask, combinations of the photolithography process and a reactive ion etching process, or combinations of the photolithography process, the reactive ion etching process, and an UV-molding process.



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